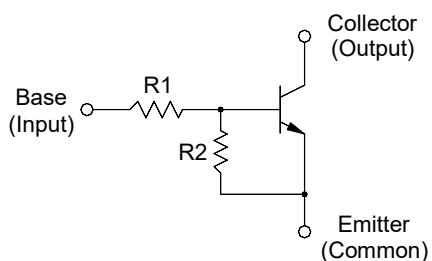


NPN Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

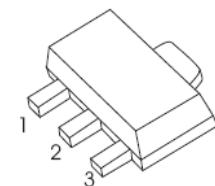
Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



SOT-89-3L

1. BASE
2. COLLECTOR
3. Emitter



Resistor Values

Type	Marking	R1 (KΩ)	R2 (KΩ)
MMBTRC101SSU	NA	4.7	4.7
MMBTRC102SSU	NB	10	10
MMBTRC103SSU	NC	22	22
MMBTRC104SSU	ND	47	47
MMBTRC105SSU	NF	2.2	47
MMBTRC106SSU	NE	4.7	47

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Output Voltage	V_O	50	V
Input Voltage	V_I	20, -10	V
		30, -10	
		40, -10	
		40, -10	
		12, -5	
		20, -5	
Output Current	I_O	100	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_O = 5 \text{ V}$, $I_O = 10 \text{ mA}$	G_I	30	-	-	-
		50	-	-	-
		70	-	-	-
		80	-	-	-
		80	-	-	-
		80	-	-	-
Output Cutoff Current at $V_O = 50 \text{ V}$	$I_{O(\text{OFF})}$	-	-	500	nA
Input Current at $V_I = 5 \text{ V}$	I_I	-	-	1.8	mA
		-	-	0.88	
		-	-	0.36	
		-	-	0.18	
		-	-	3.6	
		-	-	1.8	
Output Voltage at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$	$V_{O(\text{ON})}$	-	-	0.3	V
Input Voltage (ON) at $V_O = 0.2 \text{ V}$, $I_O = 5 \text{ mA}$	$V_{I(\text{ON})}$	-	-	2	V
		-	-	2.4	
		-	-	3	
		-	-	5	
		-	-	1.1	
		-	-	1.3	
Input Voltage (OFF) at $V_O = 5 \text{ V}$, $I_O = 0.1 \text{ mA}$	$V_{I(\text{OFF})}$	1 0.5	-	-	V
Transition Frequency at $V_O = 10 \text{ V}$, $I_O = 5 \text{ mA}$	f_T ¹⁾	-	200	-	MHz

1) Characteristic of transistor only.

